

ABSTRACT

There is provided a dry etching method that enables selective etching of an etching object containing at least one metal selected from among titanium, indium, and tin at a sufficient etching rate without using plasma. The dry etching method includes a dry etching step in which an etching gas containing a halogen fluoride, which is a compound of bromine or iodine and fluorine, is brought into contact with a member to be etched (12) having an etching object, which is an object to be etched by the etching gas, thereby etching the etching object without using plasma. The etching object contains at least one metal selected from among titanium, indium, and tin.

Fig. 1